

December 2013

FDP5800 N-Channel Logic Level PowerTrench[®] MOSFET 60 V, 80 A, 6 m Ω

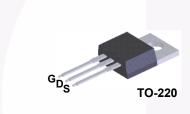
Features

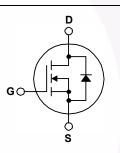
- R_{DS(on)} = 4.6 mΩ (Typ.) @ V_{GS} = 10 V, I_D = 80 A
- + High Performance Trench Technology for Extermly Low $R_{\text{DS}(\text{on})}$
- Low Gate Charge
- · High Power and Current Handing Capability
- RoHS Compliant

Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

- Applications
- Power Tools
- Motor Drives and Uninterruptible Power Supplies
- Synchronous Rectification
- Battery Protection Circuit





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

Symbol			FDP5800	Unit	
V _{DSS}	Drain-Source Voltage		60	V	
V _{GSS}	Gate-Source Voltage			±20	V
I _D		- Continuous (T _C = 25 ^o C)		80	A
	Drain Current	- Continuous (T _C = 100 ^o C)		80*	Α
		- Continuous (T _A = 25 ^o C)		14	Α
I _{DM}	Drain Current - Pulsed			320	А
E _{AS}	Single Pulsed Avalanche Energy (Note		lote 1)	652	mJ
P _D	Power Dissipation (T _C = 25 ^o C) - Derate Above 25 ^o C			242 1.61	W W/°C
T _J , T _{STG}	Operating and Storage Temperature Range			-55 to +175	°C

*Drain current limited by package.

Thermal Characteristics

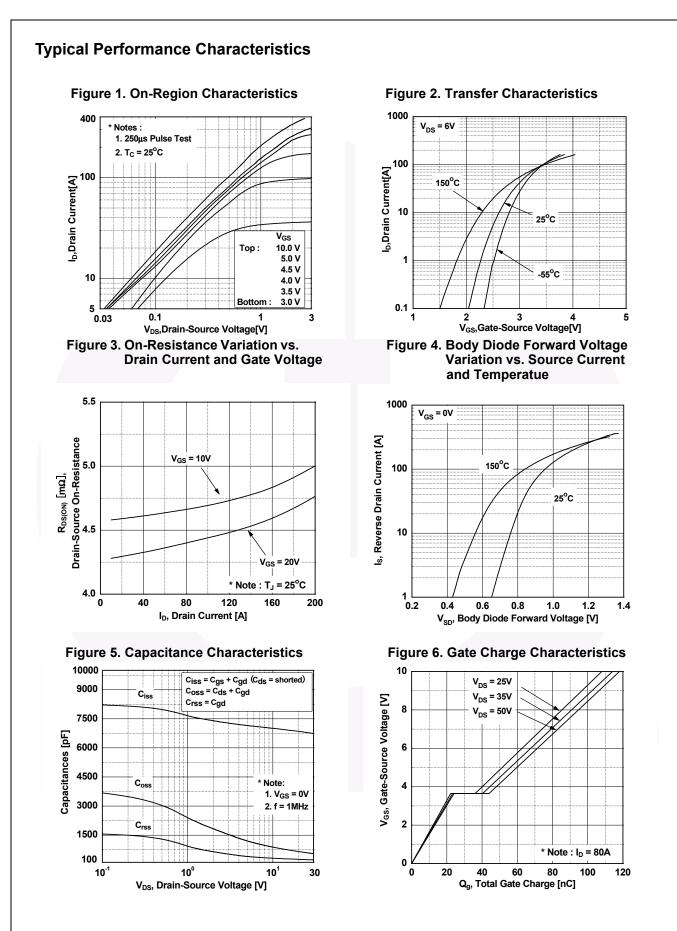
Symbol	Parameter	FDP5800	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.62	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	-0/00

1

		Package	· · ·		ze Ta	e Tape Width		Quantity	
		TO-220				N/A	50 units		
Electrica	l Chara	acteristics T _C = 2	25°C unless ot	nerwise noted.					
Symbol		Parameter		Conditi	ons	Min.	Тур.	Max.	Unit
Off Charac	teristics	5							
B _{VDSS}	Drain-So	ource Breakdown Volta	ge	I _D = 250 μA, V _{GS} =	= 0 V, T _J =25 ^o C	60			V
	Zara Ca	ta Valtaga Drain Curra	,	V _{DS} = 48 V				1	μA
DSS	Zero Gate Voltage Drain Current		п ,	$V_{GS} = 0 V$ $T_J = 150^{\circ}C$				500	μA
I _{GSS}	Gate-Body Leakage Current, Forward		orward	V _{GS} = ±20 V, V _{DS} = 0 V				±100	nA
On Charac	teristics	5							
V _{GS(th)}				V _{GS} = V _{DS} , I _D = 2	50 μΑ	1.0		2.5	V
00(01)				V _{GS} = 10 V , I _D = 8			4.6	6.0	mΩ
				V _{GS} =4.5 V , I _D = 8			5.9	7.2	mΩ
R _{DS(on)}	Static Dr	ain-Source On Resista		$V_{GS} = 5 V, I_D = 80$			5.6	7.0	mΩ
		ľ	V _{GS} =10 V, I _D = 80 T _J = 175°C			10.4	12.6	mΩ	
Dynamic C	Characte	ristics							
C _{iss}	Input Capacitance						6890	9160	pF
C _{oss}	•	Capacitance		$V_{DS} = 15 V, V_{GS} = 0 V,$			750	1000	pF
C _{rss}	-	Transfer Capacitance		_f = 1 MHz		295	445	pF	
R _G		sistance		V _{GS} = 0.5 V, f = 1	MHz		1.2		Ω
Q _{g(TOT)}	Total Gate Charge at 10V			$V_{GS} = 0 V \text{ to } 10 V$			112	145	nC
Q _{g(TH)}		te Charge at 5V		$V_{oo} = 0 V to 5 V$			58		nC
Q _{g(TH)}	Thresho	ld Gate Charge		$V_{GS} = 0 V \text{ to } 1 V$	$V_{DS} = 30 V$,		7.0		nC
Q _{gs}	Gate to	Source Gate Charge			$I_{\rm D} = 80 \text{ A},$ $I_{\rm a} = 1 \text{ mA}$		23		nC
Q _{gs2}	Gate Ch	arge Threshold to Plate	eau	i _g = 1 mA			13		nC
Q _{gd}		Drain "Miller" Charge					18		nC
	Charact	teristics (V _{GS} = 10V)							
t _{on}	Turn-On						37	85	ns
t _{d(on)}	Turn-On	Turn-On Delay Time Turn-On Rise Time					18	46	ns
t _r	Turn-On			$V_{DD} = 30 \text{ V}, \text{ I}_{D} = 80 \text{ A},$			19	47	ns
t _{d(off)}		Delay Time		$V_{GS} = 10 \text{ V}, \overline{R}_{G} = 1.5 \Omega$			55	120	ns
t _f		Fall Time					9	28	ns
t _{OFF}	Turn-Off Time						64	138	ns
	rce Dioc	le Characteristics	5						
				V _{GS} = 0 V, I _{SD} = 8	30 A			1.25	V
V _{SD}	Drain-So	ource Diode Forward V	oltage	$V_{GS} = 0 V, I_{SD} = 4$				1.0	V
t _{rr}	Reverse	Recovery Time		$V_{GS} = 0 V, I_{SD} = 60 A,$			58		ns
Q _{rr}	Reverse Recovery Charge			$dI_{F}/dt = 100 A/\mu s$,		106		nC

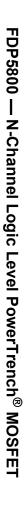
Notes: 1: L = 1 mH, I_{AS} = 36 A, V_{DD} = 54 V, V_{GS} = 10 V, R_G = 25 Ω , Starting T_J = 25^oC

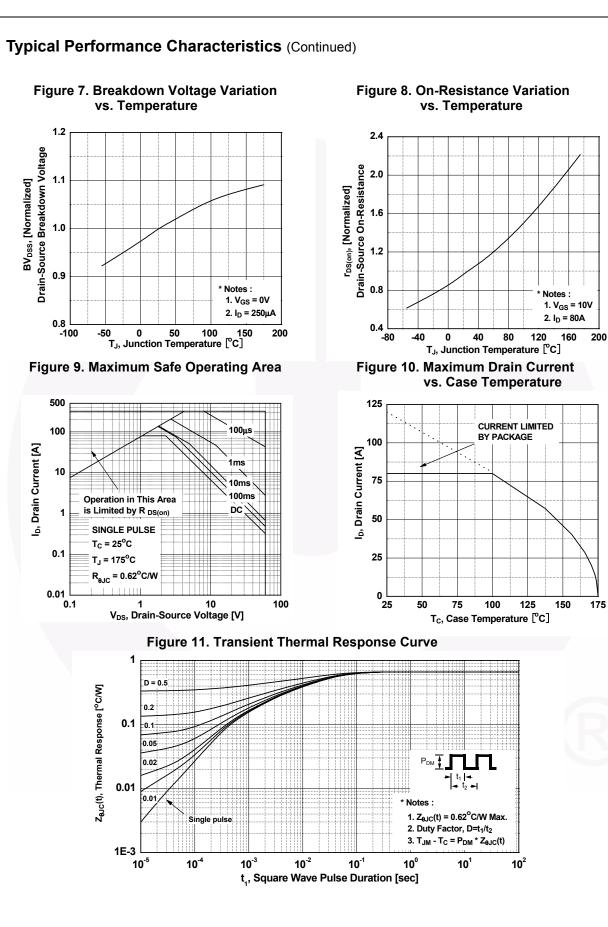
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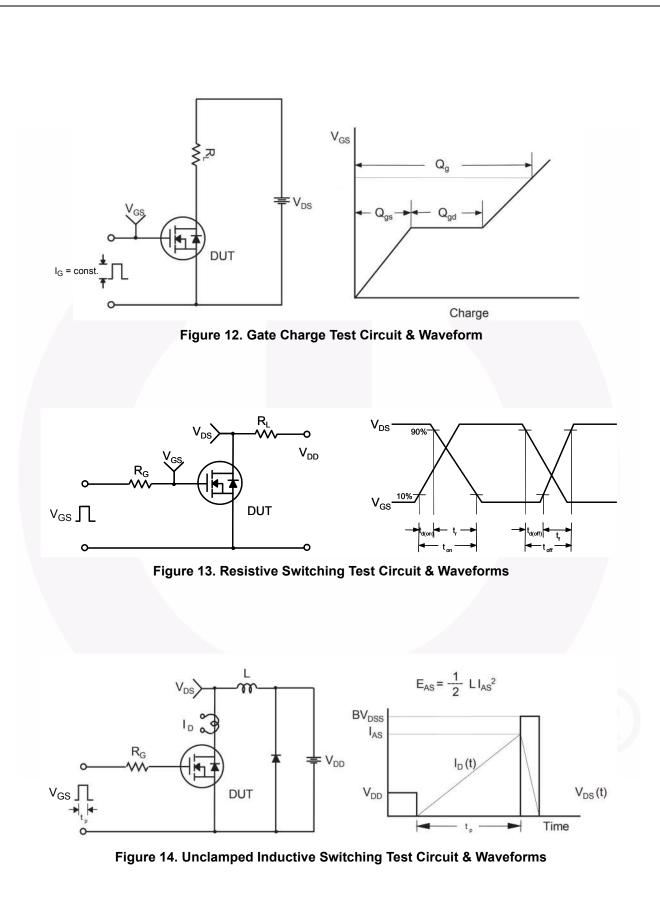


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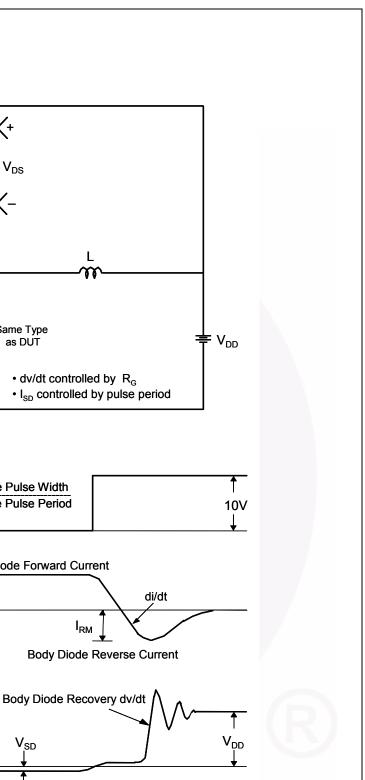
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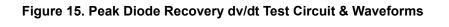






FDP5800 — N-Channel Logic Level PowerTrench[®] MOSFET





 V_{SD}

Body Diode Forward Voltage Drop

DUT

Driver

D =

R_G,

 $\prod V_{GS}$

V_{GS}

(Driver)

I _{SD}

(DUT)

 V_{DS} (DUT)

a ۱_{SD} م +

 v_{DS}

Same Type as DUT

Gate Pulse Width

Gate Pulse Period

I_{FM}, Body Diode Forward Current

 I_{RM}

L

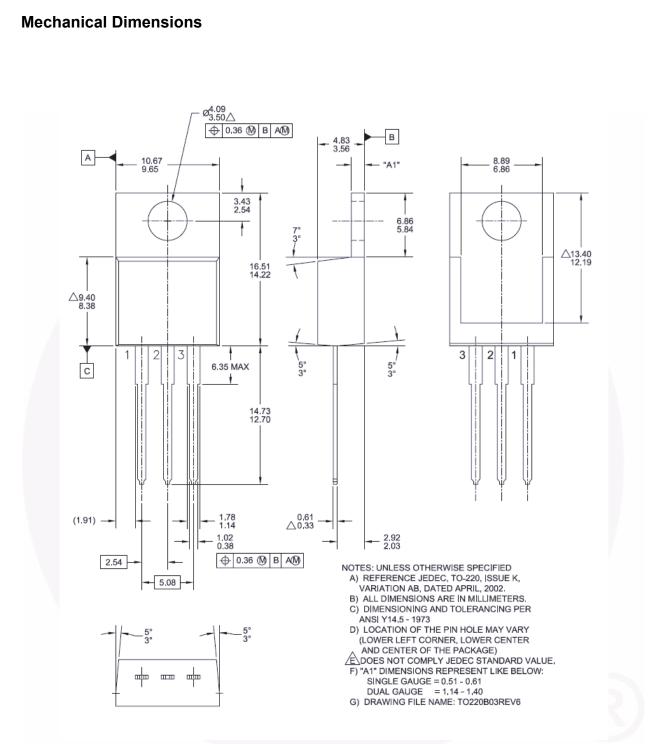


Figure 16. TO-220, Molded, 3-Lead, Jedec Variation AB

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